HFZT

2SB624

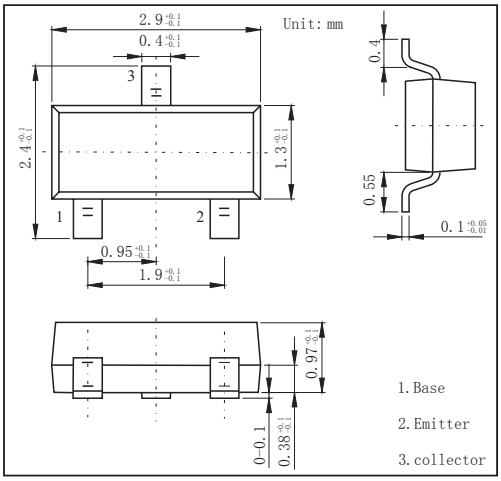
SOT-23 Plastic-Encapsulate Transistors

FEATURES

- Hgh DC current gain
- hFE:200 TYP.(VCE=-1V,IC=-100mA)
- PNP Transistor

MECHANICAL DATA

- Case style:SOT-23molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-30	V
Collector - Emitter Voltage	V_{CEO}	-25	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-700	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -100 μA, I_E=0	-30			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -1 mA, I_B=0	-25			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100 μ A, I_C=0	-5			
Collector-base cut-off current	I_{CBO}	V_{CB}= -30 V , I_E=0			-100	nA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V , I_C=0			-100	
Collector-emitter saturation voltage (Note.1)	$V_{CE(sat)}$	I_C=-700 mA, I_B=-70mA			-0.6	V
Base - emitter saturation voltage (Note.1)	$V_{BE(sat)}$	I_C=-700 mA, I_B=-70mA			-1.2	
Base - emitter voltage (Note.1)	V_{BE}	V_{CE}= -6V, I_C= -10mA	-0.6		-0.7	
DC current gain (Note.1)	$h_{FE(1)}$	V_{CE}= -1V, I_C= -100mA	110		400	
	$h_{FE(2)}$	V_{CE}=- 1V, I_C= -700mA	50			
Collector output capacitance	C_{ob}	V_{CB}= -6V, I_E= 0,f=1MHz		17		pF
Transition frequency	f_T	V_{CE}= -6V, I_C= -10mA		160		MHz

Note.1:Pulse test : Pulse width ≤350μs,Duty Cycle≤2%